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Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

MMBT2222AWT1G, SMMBT2222AWT1G

General Purpose Transistor

NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT−323/SC−70 package which is designed for low power surface mount applications.

Features

- AEC−Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	40	Vdc
Collector−Base Voltage	V_{CBO}	75	Vdc
Emitter−Base Voltage	V_{EBO}	6.0	Vdc
Collector Current − Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board T_A = 25°C	P_D	150	mW
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	280	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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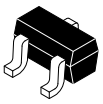
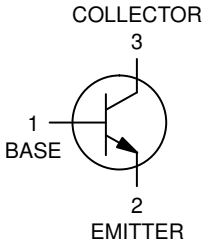
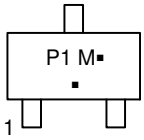


SC−70
CASE 419
STYLE 3



MARKING DIAGRAM



P1 = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MMBT2222AWT1G	SC−70 (Pb−Free)	3,000 / Tape & Reel
SMMBT2222AWT1G	SC−70 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 1) (I_C = 10 mAdc, I_B = 0)		$V_{(BR)CEO}$	40	–	Vdc
Collector – Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)		$V_{(BR)CBO}$	75	–	Vdc
Emitter – Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	6.0	–	Vdc
Base Cutoff Current (V_{CE} = 60 Vdc, V_{EB} = 3.0 Vdc)		I_{BL}	–	20	nAdc
Collector Cutoff Current (V_{CE} = 60 Vdc, V_{EB} = 3.0 Vdc)		I_{CEX}	–	10	nAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain (Note 1) (I_C = 0.1 mAdc, V_{CE} = 10 Vdc) (I_C = 1.0 mAdc, V_{CE} = 10 Vdc) (I_C = 10 mAdc, V_{CE} = 10 Vdc) (I_C = 150 mAdc, V_{CE} = 10 Vdc) (I_C = 500 mAdc, V_{CE} = 10 Vdc)		H_{FE}	 35 50 75 100 40	 – – – 300 –	–
Collector – Emitter Saturation Voltage (Note 1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{CE(sat)}$	 – –	 0.3 1.0	Vdc
Base – Emitter Saturation Voltage (Note 1) (I_C = 150 mAdc, I_B = 15 mAdc) (I_C = 500 mAdc, I_B = 50 mAdc)		$V_{BE(sat)}$	 0.6 –	 1.2 2.0	Vdc
SMALL – SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I_C = 20 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)		f_T	300	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)		C_{obo}	–	8.0	pF
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	–	30	pF
Input Impedance (V_{CE} = 10 Vdc, I_C = 10 mAdc, f = 1.0 kHz)		h_{ie}	0.25	1.25	kΩ
Voltage Feedback Ratio (V_{CE} = 10 Vdc, I_C = 10 mAdc, f = 1.0 kHz)		h_{re}	–	4.0	X 10^{-4}
Small – Signal Current Gain (V_{CE} = 10 Vdc, I_C = 10 mAdc, f = 1.0 kHz)		h_{fe}	75	375	–
Output Admittance (V_{CE} = 10 Vdc, I_C = 10 mAdc, f = 1.0 kHz)		h_{oe}	25	200	μmhos
Noise Figure (V_{CE} = 10 Vdc, I_C = 100 μAdc, R_S = 1.0 kΩ, f = 1.0 kHz)		NF	–	4.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V_{CC} = 3.0 Vdc, V_{BE} = – 0.5 Vdc, I_C = 150 mAdc, I_{B1} = 15 mAdc)	t_d	–	10	ns
Rise Time		t_r	–	25	
Storage Time	(V_{CC} = 30 Vdc, I_C = 150 mAdc, I_{B1} = I_{B2} = 15 mAdc)	t_s	–	225	ns
Fall Time		t_f	–	60	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

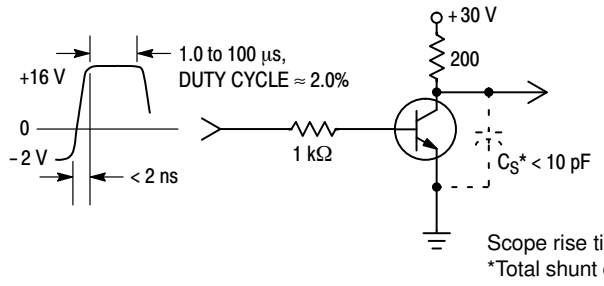


Figure 1. Turn−On Time

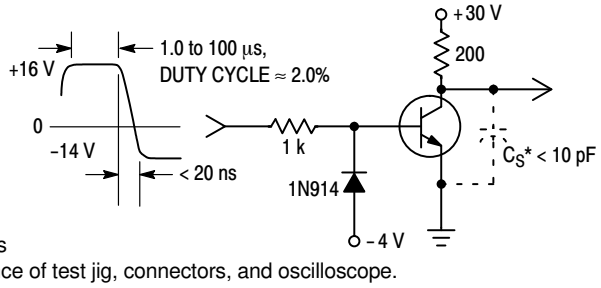


Figure 2. Turn−Off Time

Scope rise time < 4 ns
*Total shunt capacitance of test jig, connectors, and oscilloscope.

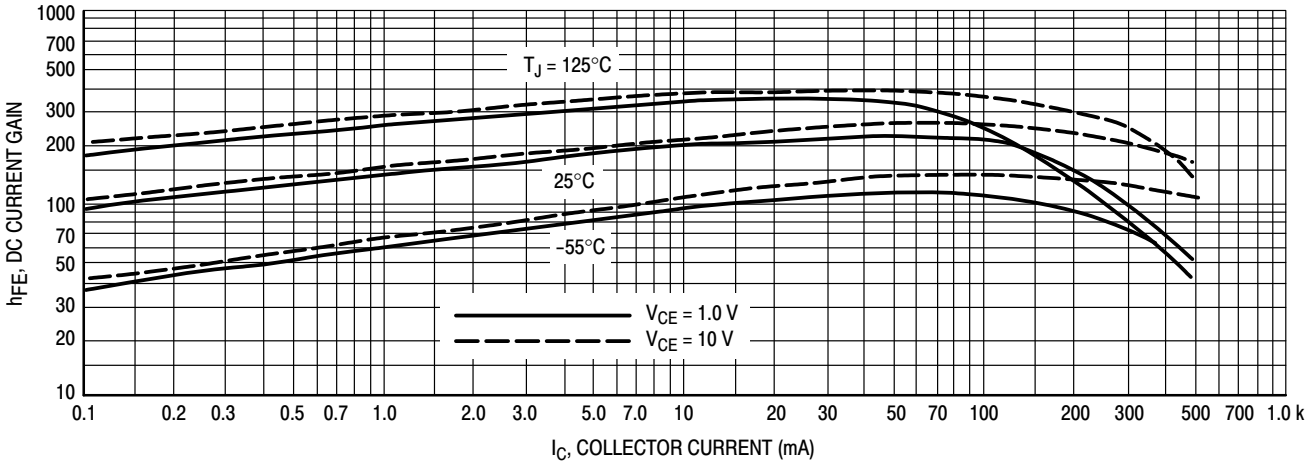


Figure 3. DC Current Gain

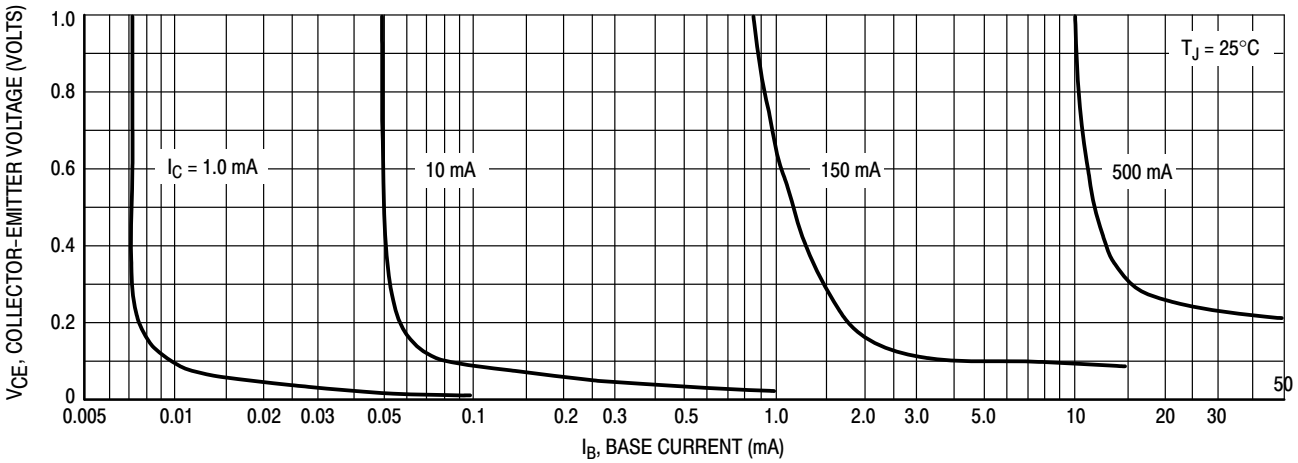


Figure 4. Collector Saturation Region

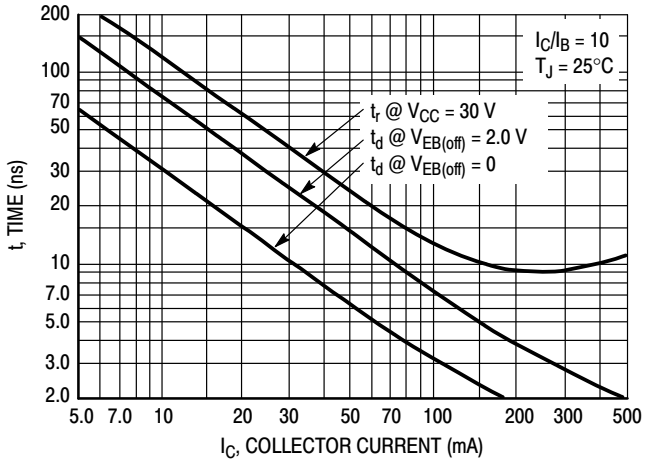


Figure 5. Turn−On Time

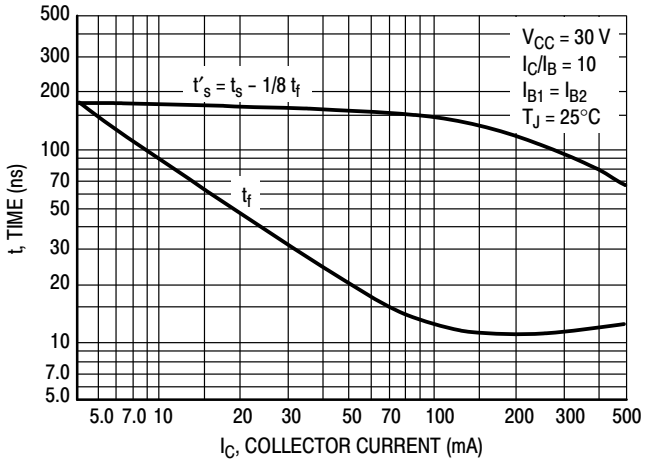


Figure 6. Turn−Off Time

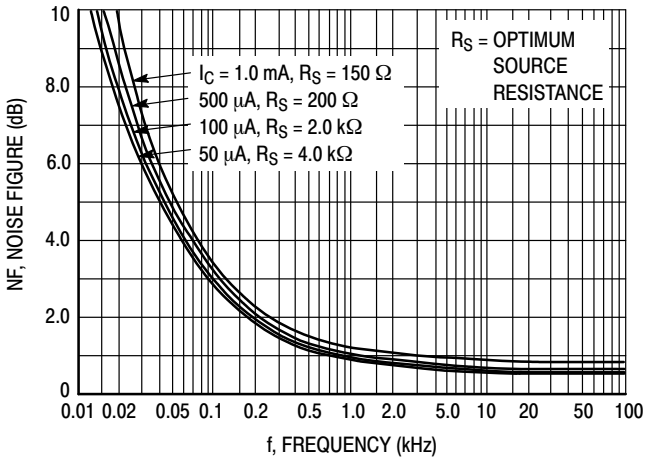


Figure 7. Frequency Effects

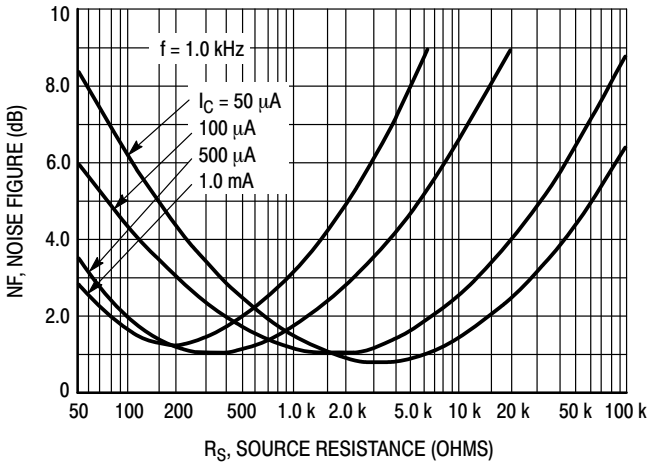


Figure 8. Source Resistance Effects

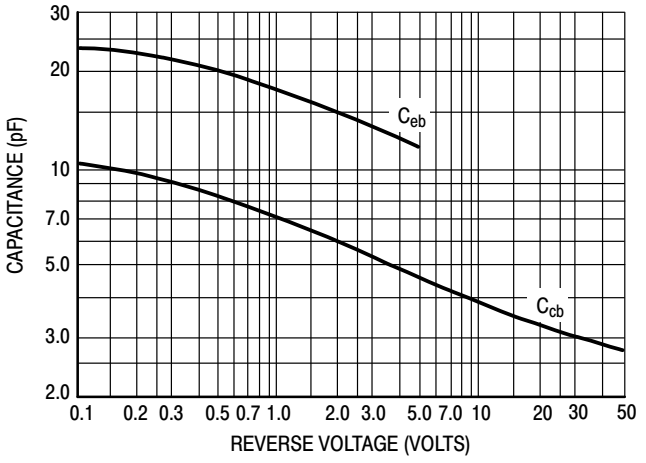


Figure 9. Capacitances

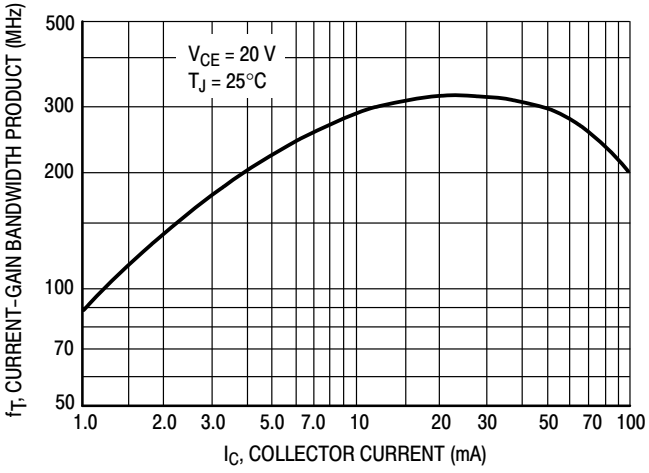


Figure 10. Current−Gain Bandwidth Product

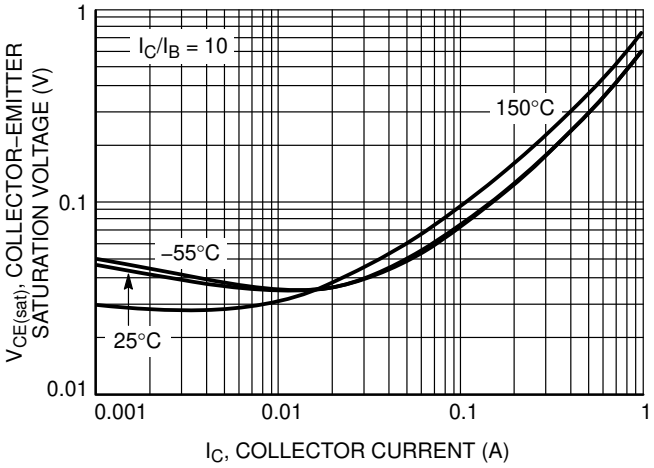


Figure 11. Collector Emitter Saturation Voltage vs. Collector Current

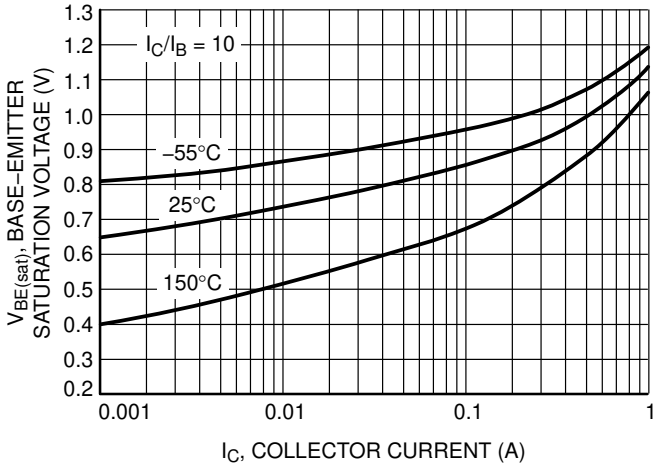


Figure 12. Base Emitter Saturation Voltage vs. Collector Current

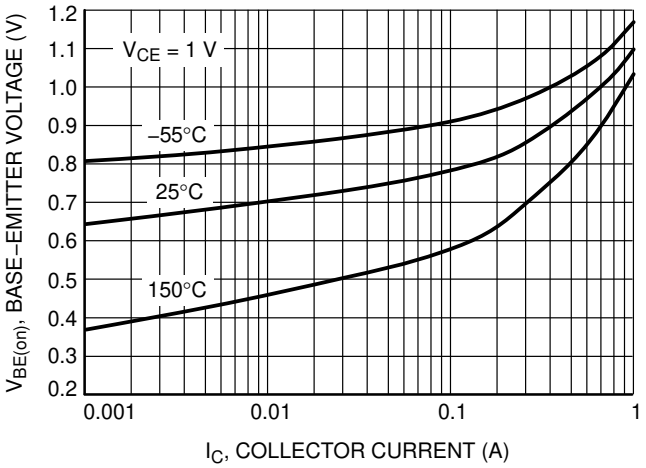


Figure 13. Base Emitter Voltage vs. Collector Current

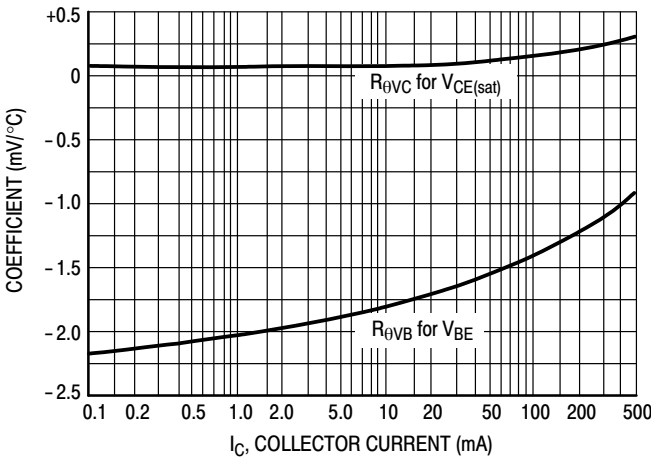


Figure 14. Temperature Coefficients

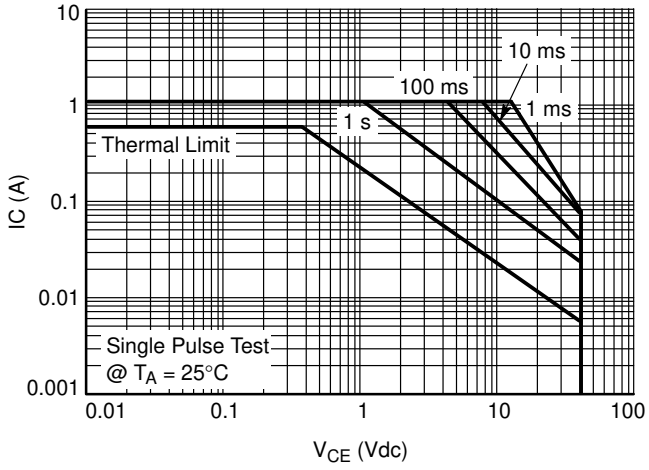
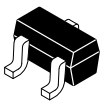


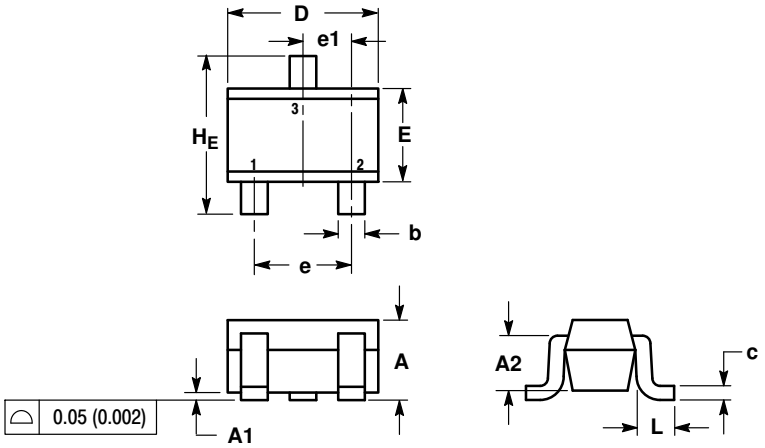
Figure 15. Safe Operating Area

SC–70 (SOT–323)
CASE 419–04
ISSUE N

DATE 11 NOV 2008



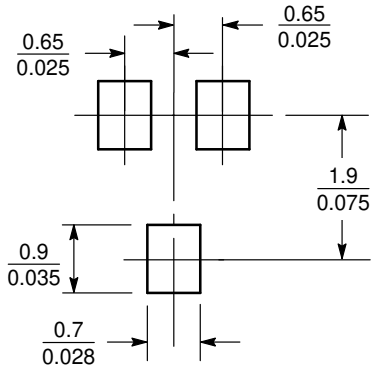
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	
L	0.20	0.38	0.56	0.008	0.015	0.022
H_E	2.00	2.10	2.40	0.079	0.083	0.095

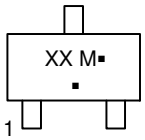
SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb–Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE–ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE–CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

ISSUE	REVISION	DATE
M	ADDED NOMINAL VALUES AND UPDATED GENERIC MARKING DIAGRAM. REQ. BY HONG XIAO	27 MAY 2005
N	CHANGED DIMENSION L VALUES TO 0.20, 0.38, 0.56 MM & 0.008, 0.015, 0.022 INCH. REQ. BY D. TRUHITTE.	11 NOV 2008

PUBLICATION ORDERING INFORMATION

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